

Advanced N-Ch Power MOSFET

SWITCHING REGULATOR APPLICATIONS

Features

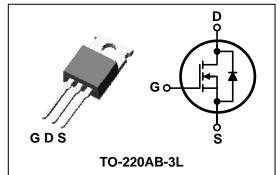
• High Voltage: BV_{DSS}=600V(Min.)

• Low C_{rss} : C_{rss} =18pF(Typ.) • Low gate charge : Qg=35nc(Typ.) • Low $R_{DS(on)}:R_{DS(on)}=0.75\Omega(Max.)$

Ordering Information

Type No.	Marking	Package Code
SMK1060P	SMK1060	TO-220AB-3L

PIN Connection



Absolute maximum ratings (T_C=25°C unless otherwise noted)

Characteristic		Symbol		Rating	Unit		
Drain-source voltage		V_{DSS}		600	V		
Gate-source voltage		V_{GSS}		±30	V		
Drain current (DC)*		т	(Tc=25℃)	10	Α		
Diani current (DC)		${ m I}_{ m D}$	(Tc=100°C)	6.32	Α		
Drain current (Pulsed)*		I_{DM}		I_{DM}		40	Α
Drain power dissipation		P _D		120	W		
Avalanche current (Single)	2	I _{AS}		10	А		
Single pulsed avalanche energy	2	E _{AS}		490	mJ		
Avalanche current (Repetitive)	1	I_{AR}		10	Α		
Repetitive avalanche energy	1	E _{AR}		E _{AR}		11.6	mJ
Junction temperature		T _J		150	°C		
Storage temperature range		T _{stg}		-55~150	1		

^{*} Limited by maximum junction temperature

Cha	racteristic	Symbol	Typ.	Max	Unit
Thermal	Junction-case	$R_{th(J-C)}$	ı	1.04	°C/W
resistance	Junction-ambient	$R_{th(J-a)}$	-	62.5	C/ VV

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$\boldsymbol{Electrical\ Characteristics}\ (T_{C}\text{=}25^{\circ}C\ unless\ otherwise\ noted})$

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$I_D = 250 \mu A, V_{GS} = 0$	600	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu A$, $V_{DS}=V_{GS}$	2.0	ı	4.0	V
Drain-source cut-off current	I_{DSS}	V _{DS} =600V, V _{GS} =0V	-	-	1	μΑ
Gate leakage current	I_{GSS}	V_{DS} =0V, V_{GS} =±30V	-	-	±100	nA
Drain-source on-resistance 4	R _{DS(ON)}	V _{GS} =10V, I _D =5.0A	-	0.60	0.75	Ω
Forward transfer conductance 4	9 _{fs}	V _{DS} =10V, I _D =5.0A	-	8.0	-	S
Input capacitance	Ciss	V _{GS} =0V, V _{DS} =25V	-	2000	2350	
Output capacitance	Coss	f=1MHz	-	160	215	pF
Reverse transfer capacitance	Crss		-	18	-	
Turn-on delay time	t _{d(on)}		-	23	-	
Rise time	t _r	V_{DD} =300V, I_{D} =10A R_{G} =25 Ω	-	69	-	20
Turn-off delay time	t _{d(off)}	34	-	144	-	ns
Fall time	t _f		-	77	-	
Total gate charge	Q_g	V _{DS} =480V, V _{GS} =10V	-	35	57	
Gate-source charge	Q_{gs}	$I_D=10A$	-	9.0	-	nC
Gate-drain charge	Q_{gd}	34	-	10	-	

Source-Drain Diode Ratings and Characteristics (T_C=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Тур	Max	Unit
Source current (DC)	I_{S}	Integral reverse diode	-	-	10	А
Source current (Pulsed)	1 I _{SM}	in the MOSFET		-	40	A
Forward voltage	4 V _{SD}	V _{GS} =0V, I _S =10A	-	-	1.4	V
Reverse recovery time	t _{rr}	I _s =10A, V _{GS} =0, di _s /dt=100A/ us	-	470	-	ns
Reverse recovery charge	Q_{rr}	di _S /dt=100A/ us	-	6	-	uC

Note;

① Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

② L=10mH, I_{AS} =9.5A, V_{DD} =50V, R_{G} =25 Ω , Starting T_{J} = 25 $^{\circ}$ C

③ Pulse Test : Pulse Width < 300us, Duty cycle ≤ 2%

4 Essentially independent of operating temperature

Electrical Characteristic Curves

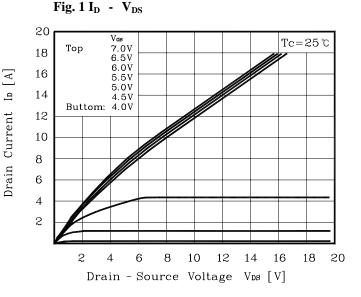


Fig. 2 $I_D\,$ - $\,V_{GS}\,$

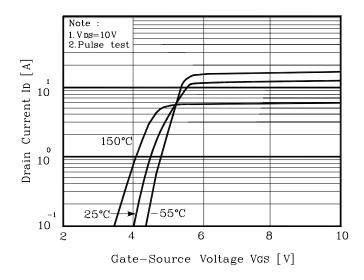


Fig. 3 $R_{DS(on)}$ - I_D

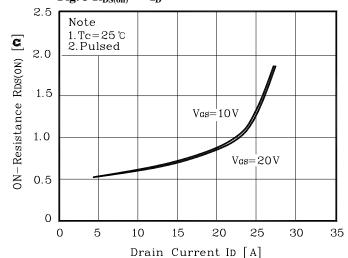


Fig. 4 I_S - V_{SD}

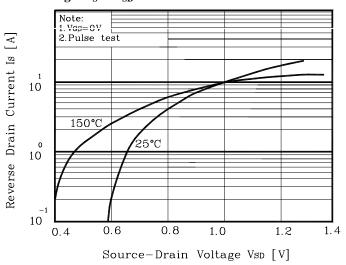


Fig. 5 Capacitance - V_{DS}

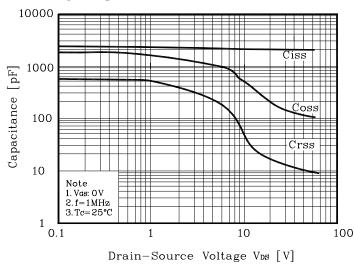
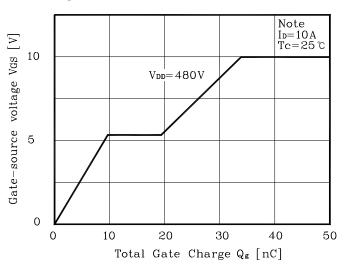


Fig.6 V_{GS} - Q_{G}



Electrical Characteristic Curves

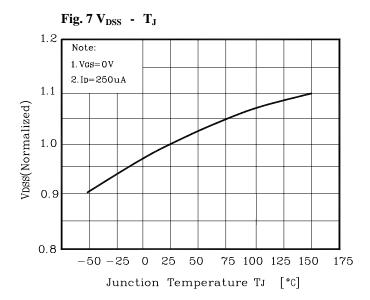


Fig. 9 I_D - T_C

10.0

8.0

[V]

6.0

25

50

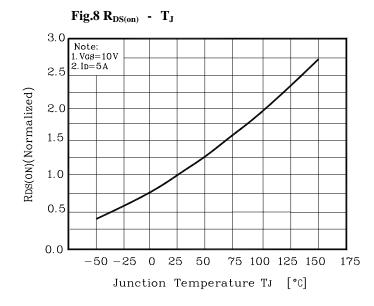
75

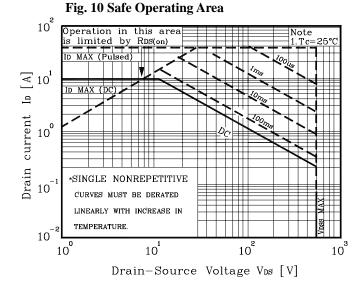
100

125

150

Case Temperature Tc [°C]





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Fig. 10 Gate Charge Test Circuit & Waveform

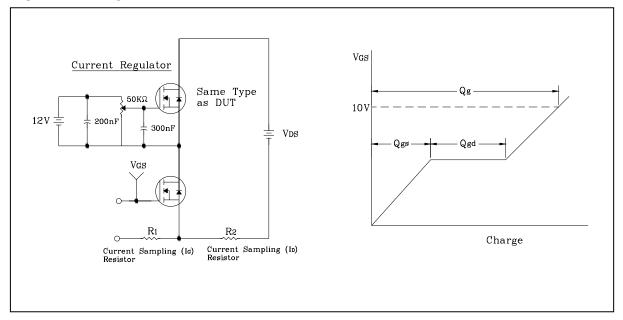


Fig. 11 Resistive Switching Test Circuit & Waveform

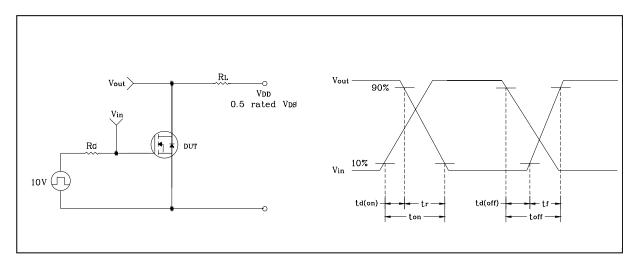
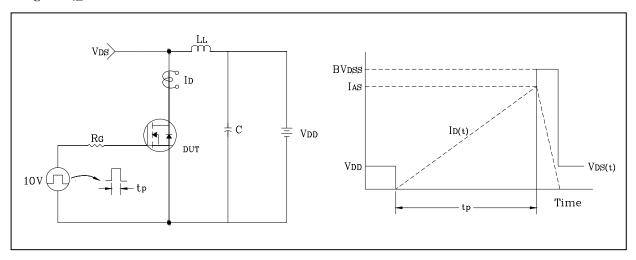
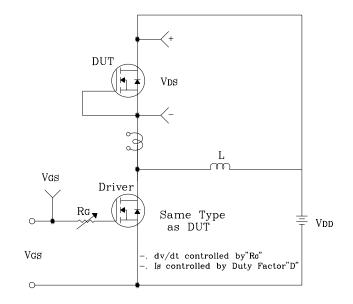


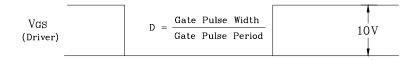
Fig. 12 E_{AS} Test Circuit & Waveform

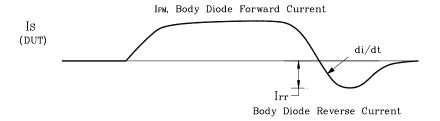


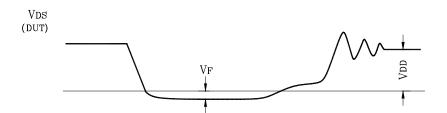
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Fig. 13 Diode Reverse Recovery Time Test Circuit & Waveform

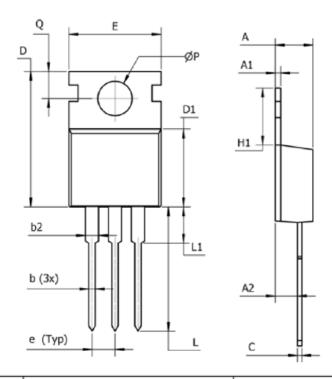








Outline Dimension



DIM	ММ	INCHES
D	14.22-16.51	0.560-0.650
ØP	Ø3.53-4.09	Ø0.139-0.161
H1	5.84-6.86	0.230-0.270
b	0.38-1.02	0.015-0.040
b2	1.14-1.78	0.045-0.070
D1	8.38-9.02	0.330-0.355
е	2.54	0.100
E	9.65-10.67	0.380-0.420
L1	6.35(MAX)	0.250(MAX)
Α	3.56-4.83	0.140-0.190
A1	0.51-0.71	0.020-0.028
L	12.70-14.73	0.500-0.580
A2	2.03-2.92	0.080-0.115
Q	2.54-3.43	0.100-0.135
С	0.36-0.61	0.014-0.024

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